

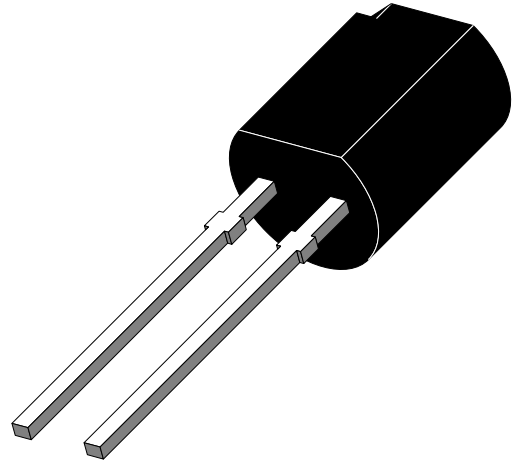
## Silicon PIN Photodiode

### Description

BPV21F is a high speed and high sensitive PIN photodiode in a plastic package with a cylindrical side view lens. The epoxy package itself is an IR filter, spectrally matched to GaAs or GaAs/GaAlAs IR emitters ( $\lambda_p = 950$  nm).

Lens radius and chip position are perfectly matched to the chip size, giving high sensitivity without compromising the viewing angle.

In comparison with flat packages the cylindrical lens package achieves a sensitivity improvement of 20 %.



94 8387

### Features

- Large radiant sensitive area ( $A = 5.7 \text{ mm}^2$ )
- Wide viewing angle  $\varphi = \pm 65^\circ$
- Fast response times
- Low junction capacitance
- TO-92 plastic package with IR filter
- Filter designed for 950 nm transmission

### Applications

Infrared remote control and free air transmission systems in combination with IR emitter diodes (TSU...- or TSI...-Series).

### Absolute Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$

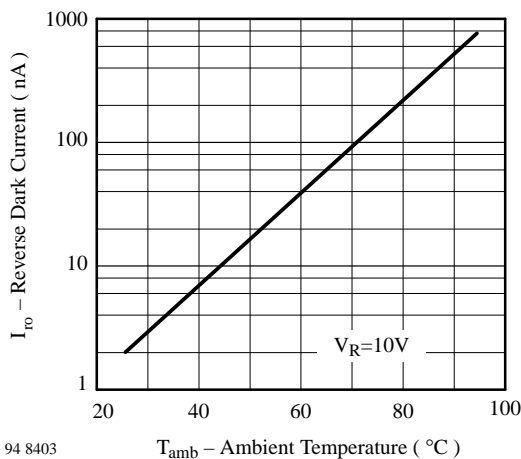
Parameter	Test Conditions	Symbol	Value	Unit
Reverse Voltage		$V_R$	60	V
Power Dissipation	$T_{\text{amb}} \leq 25^\circ\text{C}$	$P_V$	215	mW
Junction Temperature		$T_j$	100	$^\circ\text{C}$
Operating Temperature Range		$T_{\text{amb}}$	-55...+100	$^\circ\text{C}$
Storage Temperature Range		$T_{\text{stg}}$	-55...+100	$^\circ\text{C}$
Soldering Temperature	$t \leq 5 \text{ s}$	$T_{\text{sd}}$	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		$R_{\text{thJA}}$	350	K/W

## Basic Characteristics

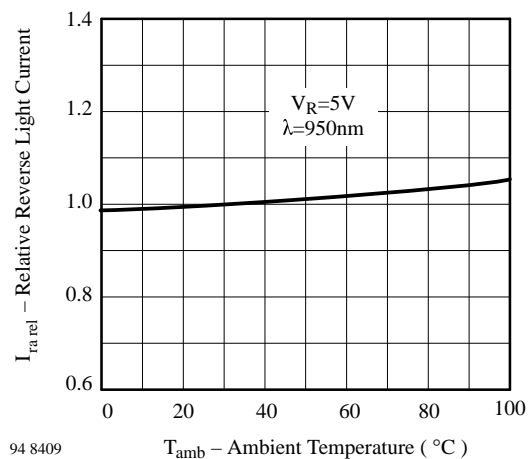
$T_{amb} = 25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	$I_F = 50\text{ mA}$	$V_F$		1	1.3	V
Breakdown Voltage	$I_R = 100\text{ }\mu\text{A}, E = 0$	$V_{(BR)}$	60			V
Reverse Dark Current	$V_R = 10\text{ V}, E = 0$	$I_{ro}$		2	30	nA
Diode Capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz}, E = 0$	$C_D$		48		pF
Serial Resistance	$V_R = 12\text{ V}, f = 1\text{ MHz}$	$R_S$		900		$\Omega$
Open Circuit Voltage	$E_c = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}$	$V_o$		380		mV
Temp. Coefficient of $V_o$	$E_c = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}$	$TK_{V_o}$		-2.6		mV/K
Short Circuit Current	$E_c = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}$	$I_k$		35		$\mu\text{A}$
Reverse Light Current	$E_c = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}, V_R = 5\text{ V}$	$I_{ra}$	27	38		$\mu\text{A}$
Temp. Coefficient of $I_{ra}$	$E_c = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}, V_R = 10\text{ V}$	$TK_{I_{ra}}$		0.1		%/K
Absolute Spectral Sensitivity	$V_R = 5\text{ V}, \lambda = 870\text{ nm}$	$s(\lambda)$		0.35		A/W
	$V_R = 5\text{ V}, \lambda = 950\text{ nm}$	$s(\lambda)$		0.6		A/W
Angle of Half Sensitivity		$\phi$		$\pm 65$		deg
Wavelength of Peak Sensitivity		$\lambda_p$		950		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		870...1050		nm
Quantum Efficiency	$\lambda = 950\text{ nm}$	$\eta$		90		%
Noise Equivalent Power	$V_R = 10\text{ V}, \lambda = 950\text{ nm}$	NEP		$4 \times 10^{-14}$		$\text{W}/\sqrt{\text{Hz}}$
Detectivity	$V_R = 10\text{ V}, \lambda = 950\text{ nm}$	$D^*$		$5 \times 10^{12}$		$\text{cm}\sqrt{\text{Hz}}/\text{W}$
Rise Time	$V_R = 10\text{ V}, R_L = 1\text{ k}\Omega, \lambda = 820\text{ nm}$	$t_r$		70		ns
Fall Time	$V_R = 10\text{ V}, R_L = 1\text{ k}\Omega, \lambda = 820\text{ nm}$	$t_f$		70		ns
Cut-Off Frequency	$V_R = 12\text{ V}, R_L = 1\text{ k}\Omega, \lambda = 870\text{ nm}$	$f_c$		4		MHz
	$V_R = 12\text{ V}, R_L = 1\text{ k}\Omega, \lambda = 950\text{ nm}$	$f_c$		1		MHz

## Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)



94 8403  $T_{amb}$  – Ambient Temperature ( $^{\circ}\text{C}$ )  
Figure 1.. Reverse Dark Current vs. Ambient Temperature



94 8409  $T_{amb}$  – Ambient Temperature ( $^{\circ}\text{C}$ )  
Figure 2.. Relative Reverse Light Current vs. Ambient Temperature

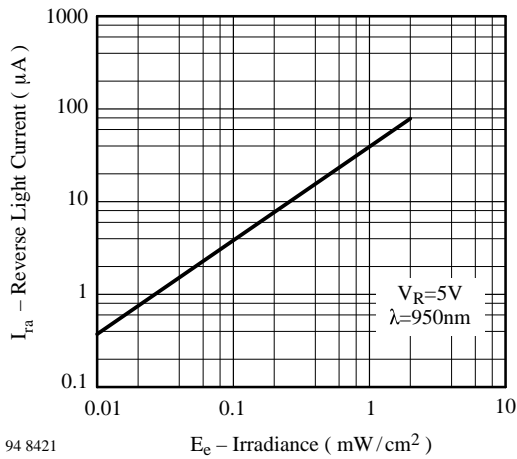


Figure 3. Reverse Light Current vs. Irradiance

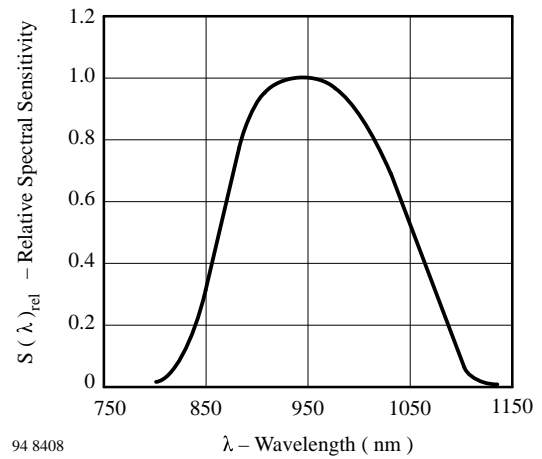


Figure 6. Relative Spectral Sensitivity vs. Wavelength

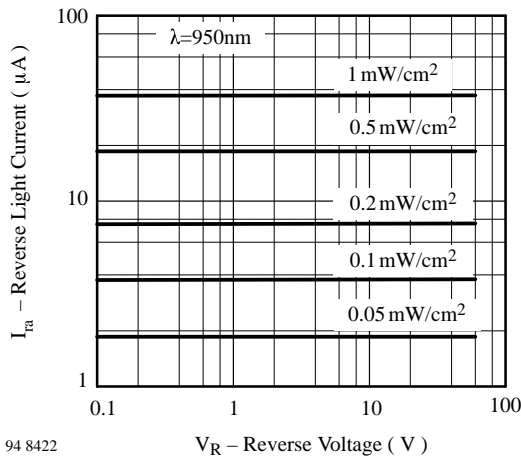


Figure 4. Reverse Light Current vs. Reverse Voltage

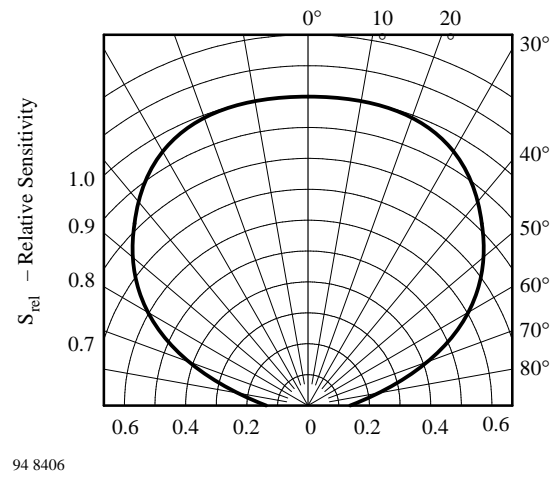


Figure 7. Relative Radiant Sensitivity vs. Angular Displacement

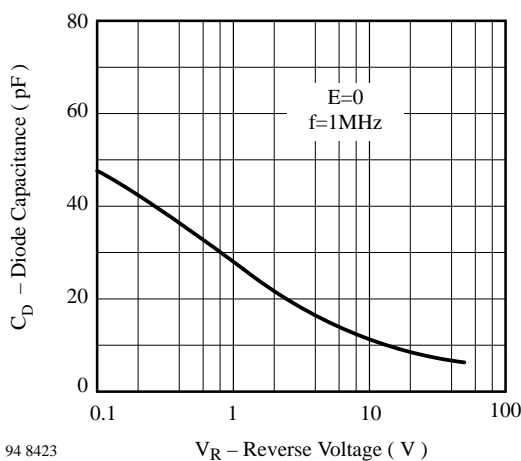
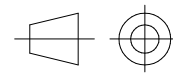
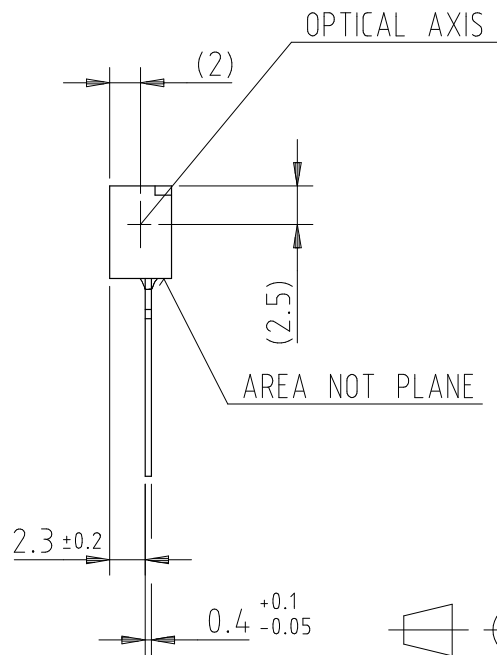
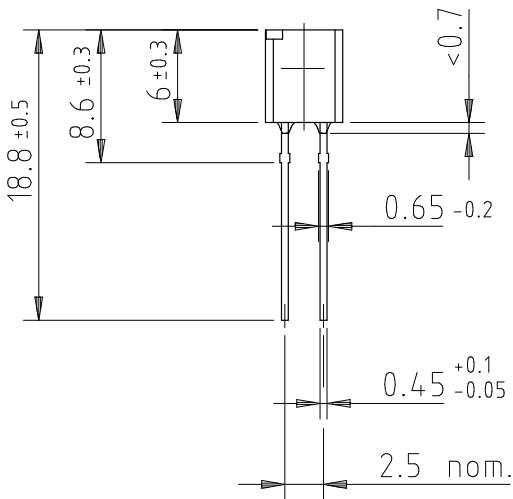
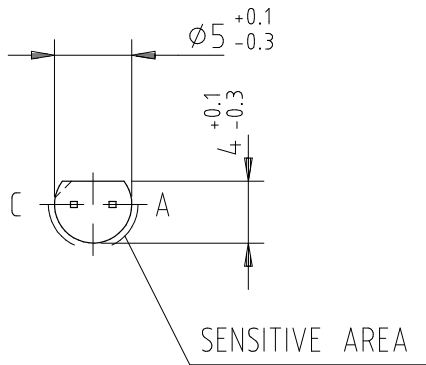


Figure 5. Diode Capacitance vs. Reverse Voltage

## Dimensions in mm



technical drawings  
according to DIN  
specifications

9612202

## Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

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